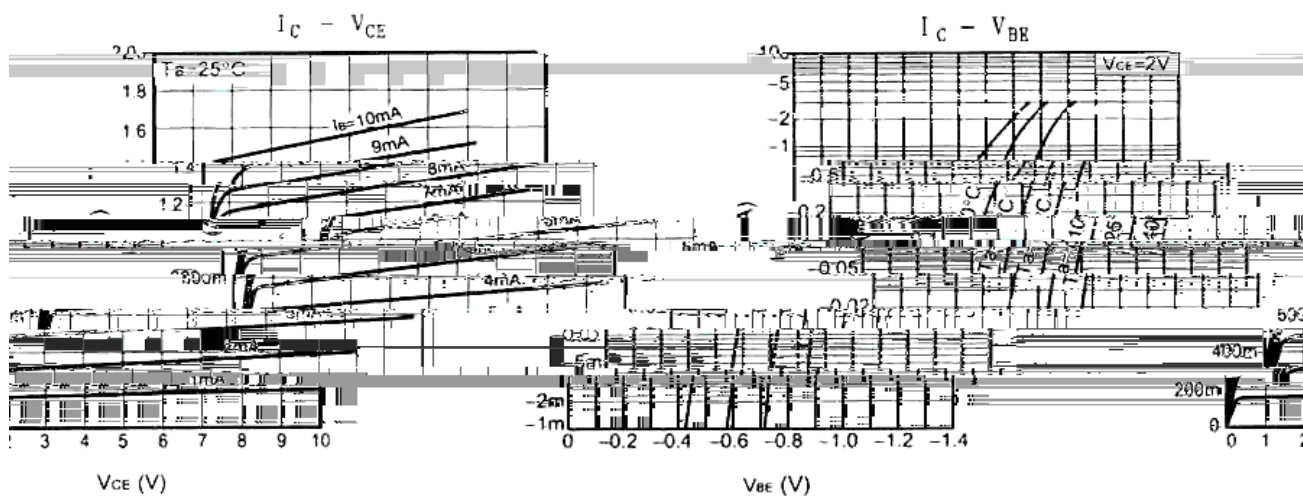
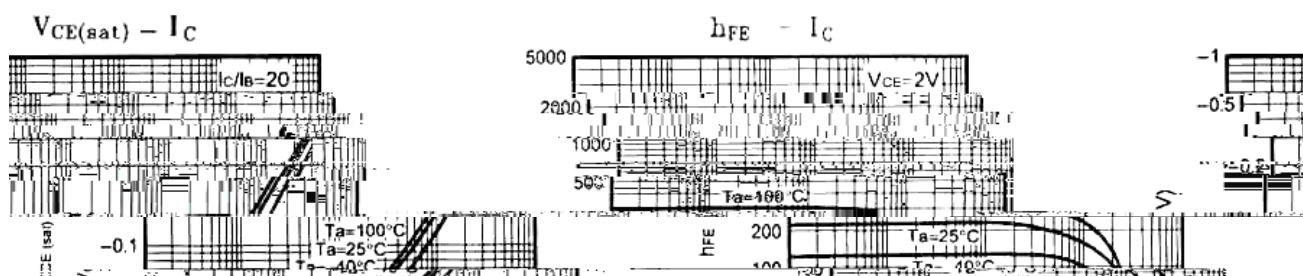


VRW0;< ММ Ё SQS æ М ы s ll 1 Silicon PNP transistor in a SOT-89 Plastic Package.

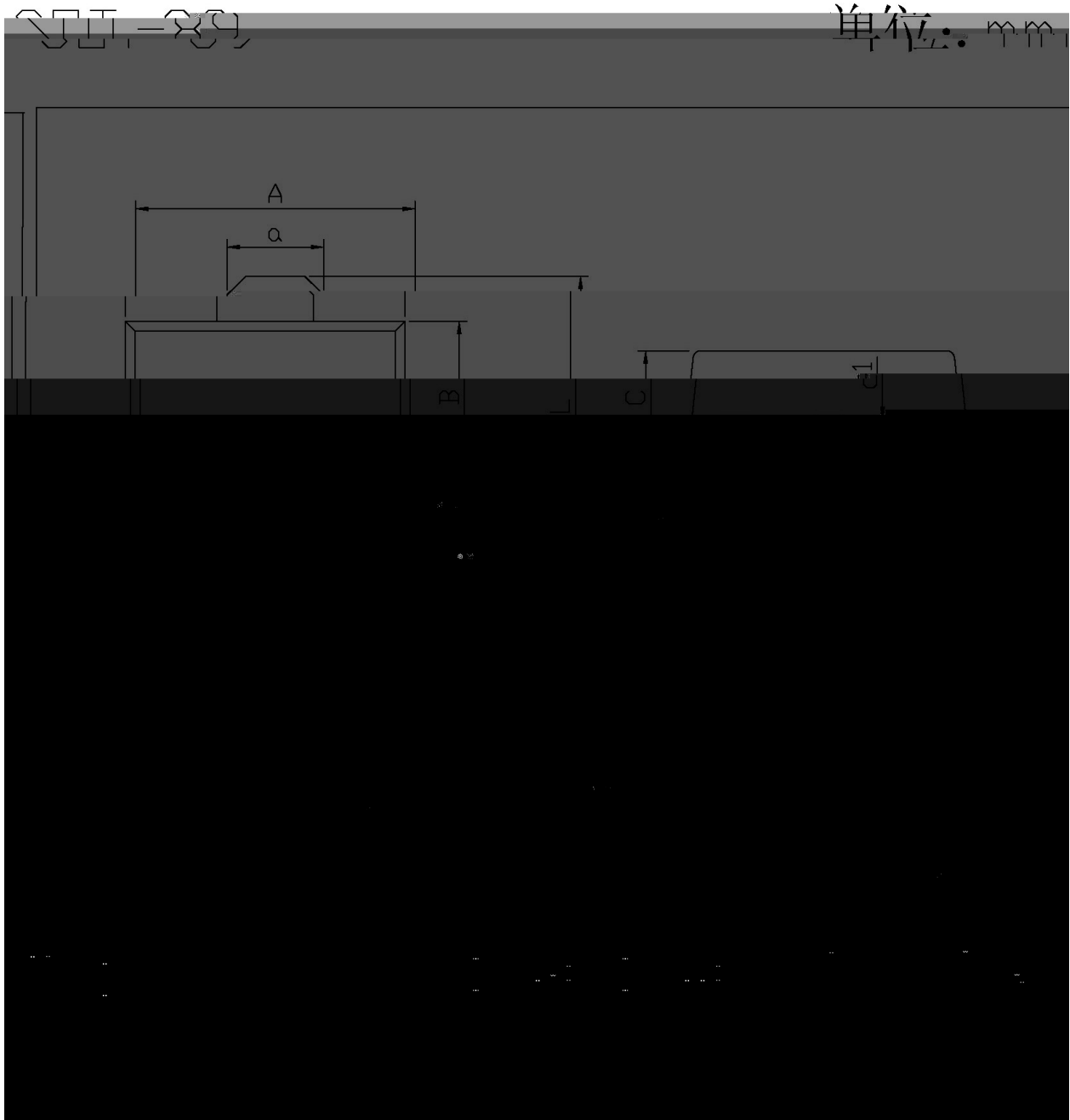
т = я ъ H/ ll B 000' ll ъ ll щ ` æ ó/лб 5VF79:5 й ´
6

Parameter	Symbol	Rating	Unit
Collector to Base Voltage	V_{CBO}	-50	V
Collector to Emitter Voltage	V_{CEO}	-50	V
Emitter to Base Voltage	V_{EBO}	-6.0	V
Collector Current-Continuous	I_C	-3.0	A
Collector Current -Continuous(Pulse)	I_{CP}	-6.0	A
Collector Power Dissipation	P_C	0.5	W
Collector Power Dissipation*	$*P_C$	2.0	W

电气特性 / Electrical Characteristic Curve



⌘ È Ò Ì f / Package Dimensions



1. 1.1 / Marking Instructions



1.1.1

HAGP

AGP

P: h_{FE}

--X

Note:

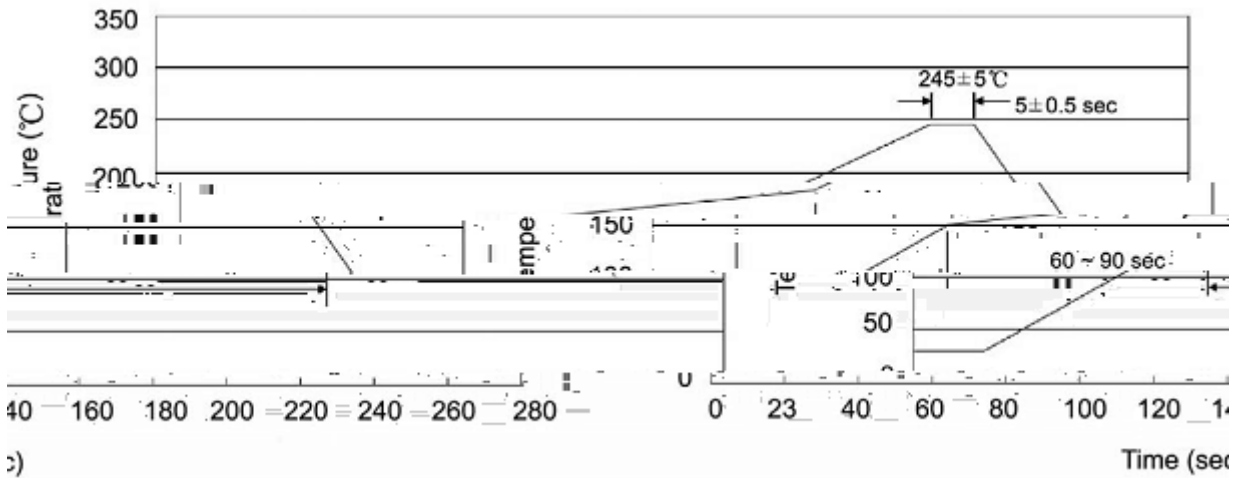
H: Company Code.

AG: Product Type.

P: h_{FE} Classifications Symbol

**:

Thermal Characteristics / 热特性



Thermal Characteristics

- Preheating: 25~150 °C, Time: 60~90sec;
- Peak Temp.: 245±5 °C, Duration: 5±0.5sec;
- Cooling Speed: 2~10 °C/sec.

Note:

- Preheating: 25~150 °C, Time: 60~90sec.
- Peak Temp.: 245±5 °C, Duration: 5±0.5sec.
- Cooling Speed: 2~10 °C/sec.

Resistance to Soldering Heat Test Conditions / 焊接热阻测试条件

Temperature: 260±5 °C, Time: 10±1 sec.

Packaging SPEC. / 封装规格

REEL

Package Type 封装形式	Units 包装数量					Dimension 包装尺寸 (unit: mm ³)		
	Units/Reel 只/卷盘	Reels/Inner Box 卷盘/盒	Units/Inner Box 只/盒	Inner Boxes/Outer Box 盒/箱	Units/Outer Box 只/箱	Reel	Inner Box 盒	Outer Box 箱
SOT-89	1,000	7	7,000	8	56,000	7 p ×12	180×120×180	385×257×392

Notices / 注意事项